

ESD0501Q

ESD Protection Diode

DESCRIPTION

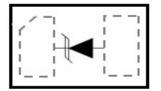
The ESD0501Q is designed for applications transient overvoltage protection requiring capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines. communication systems, medical equipment and other applications. These devices are ideal for situations where board space is at a premium.

This series has been specifically designed to protect sensitive components which are connected to power, data and transmission lines from overvoltage caused by ESD(electrostatic discharge), CDE (Cable Discharge Events),and EFT (electrical fast transients).

ORDERING INFORMATION

- ♦Device: ESD0501Q
- ♦Package: DFN1006
- ♦ Marking: FQ
- ♦Material: Halogen free
- ♦Packing: Tape & Reel
- ♦Quantity per reel: 10,000pcs

PIN CONFIGURATION



FEATURES

±8kV (Contact)

IEC 61000-4-4 (EFT) 40A (5/50 ns)

Cable Discharge Event (CDE)

- Package optimized for high-speed lines
- Ultra-small package (1.0mm×0.6mm×0.5mm)
- ♦Protects one data, control line
- ♦Low leakage current
- ♦Low clamping voltage

MACHANICAL DATA

- ♦DFN1006 package
- ♦ Flammability Rating: UL 94V-0
- ♦Packaging: Tape and Reel
- ♦ High temperature soldering guaranted:260°C/10s
- ♦Reel size: 7 inch

APPLICATIONS

- \diamond Serial ATA
- Desktops, Servers and Notebooks
- ♦ Cellular Phones
- ♦ MDDI Ports
- ♦ USB Data Line Protection
- ♦ Display Ports
- ♦ Digital Visual Interfaces (DVI)

CIRCUIT DIAGRAM





ESD0501Q

ABSOLUTE MAXIMUM RATING						
Symbol	Parameter	Value	Units			
V _{ESD}	ESD per IEC 61000-4-2 (Air)	±30	kV			
	ESD per IEC 61000-4-2 (Contact)	±30				
P _{PP}	Peak Pulse Power (8/20µs)	240	W			
Т _{орт}	Operating Temperature	-55~125	°C			
T _{STG}	Storage Temperature	-55~150	°C			

ELECTRICAL CHARACTERISTICS (Tamb=25°C)								
Symbol	Parameter	Test Condition	Min	Тур	Max	Units		
V _{RWM}	Reverse Working Voltage				5	V		
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA	6			V		
I _R	Reverse Leakage Current	V _{RWM} = 5V			1	μA		
V _F	Forward Voltage	I _F = 10mA			1.0	V		
Vc	Clamping Voltage	I _{PP} = 1A, t _p = 8/20µs			8	V		
		I _{PP} = 15Α, t _p = 8/20μs			16	V		
CJ	Junction Capacitance	V _R = 0V, f = 1MHz		130		pF		



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